



## UF460

Power MOSFET

### 21 Amps, 500 Volts N-CHANNEL POWER MOSFET

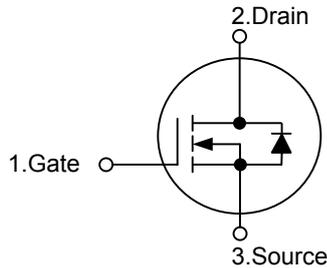
#### DESCRIPTION

The **UF460** uses advanced UTC technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with low gate voltages. This device is suitable for use as a load switch, in PWM applications, motor controls, inverters, choppers, audio amplifiers and high energy pulse circuits.

#### FEATURES

- \*  $R_{DS(ON)} = 310m\Omega @ V_{GS} = 10V, I_D = 21A$
- \* Ultra low gate charge (max. 190nC)
- \* Low reverse transfer capacitance ( $C_{RSS} = \text{typical } 250pF$ )
- \* Fast switching capability
- \* Avalanche energy specified
- \* Improved dv/dt capability

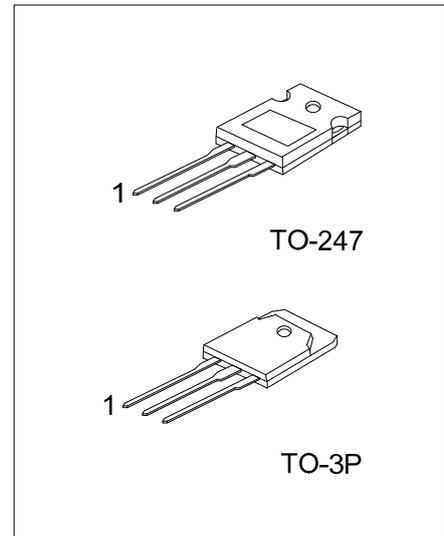
#### SYMBOL



#### ORDERING INFORMATION

Ordering Number			Package	Pin Assignment			Packing
Normal	Lead Free Plating	Halogen Free		1	2	3	
UF460-T47-T	UF460L-T3P-T	UF460G-T3P-T	TO-3P	G	D	S	Tube
UF460-T47-T	UF460L-T47-T	UF460G-T47-T	TO-247	G	D	S	Tube

<p>UF460L-T3P-T</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Lead Plating</p>	<p>(1) T: Tube</p> <p>(2) T3P: TO-3P, T47: TO-247</p> <p>(3) G: Halogen Free, L: Lead Free, Blank: Pb/Sn</p>
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Lead-free: UF460L  
Halogen-free: UF460G

## ■ ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
Gate-Source Voltage		$V_{GS}$	$\pm 20$	V
Continuous Drain Current	Continuous ( $V_{GS}=0V$ )	$I_D$	21	A
Pulsed Drain Current	Pulsed (Note 2)	$I_{DM}$	84	A
Avalanche Current (Note2)		$I_{AR}$	21	A
Avalanche Energy	Repetitive(Note2)	$E_{AR}$	30	mJ
	Single Pulsed(Note3)	$E_{AS}$	1200	
Power Dissipation ( $T_C=25^\circ C$ )		$P_D$	190	W
Peak Diode Recovery dv/dt (Note4)		dv/dt	3.5	V/ns
Junction Temperature		$T_J$	+150	$^\circ C$
Strong Temperature		$T_{STG}$	-55 ~ +150	$^\circ C$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Pulse width limited by  $T_{J(MAX)}$

3.  $V_{DD}=50V$ , Starting  $T_J=25^\circ C$ , Peak  $I_L=21A$

4.  $I_{SD}\leq 21A$ ,  $di/dt\leq 160A/\mu s$ ,  $V_{DD}\leq 500V$ ,  $T_J\leq 150^\circ C$ , Suggested=2.35 $\Omega$

## ■ THERMAL DATA

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
Junction to Ambient	$\theta_{JA}$			30	$^\circ C/W$
Junction to Case	$\theta_{JC}$			0.42	$^\circ C/W$

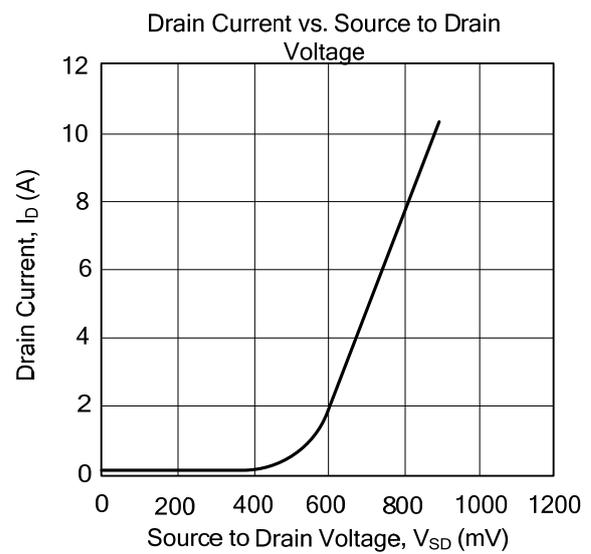
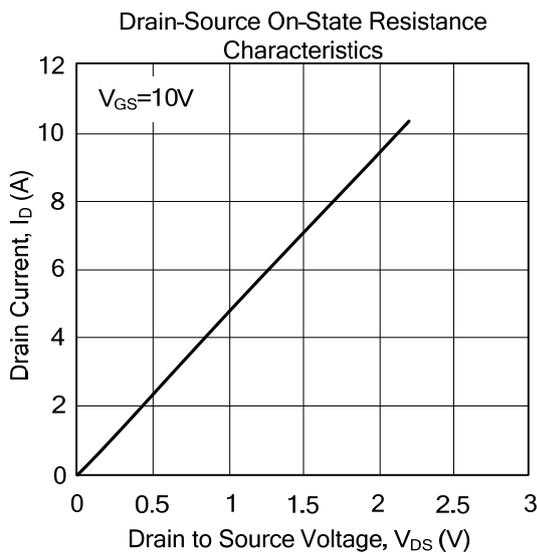
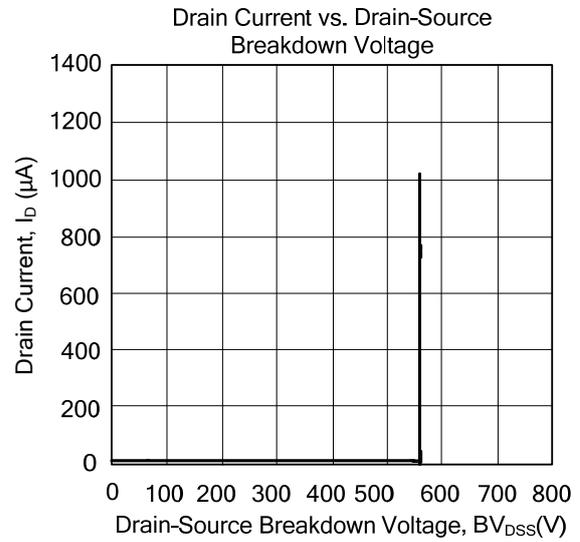
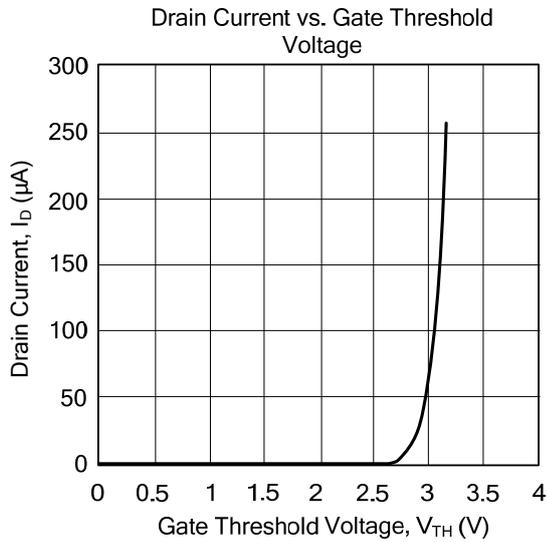
## ■ ELECTRICAL CHARACTERISTICS ( $T_J=25^\circ C$ , unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	500			V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS}=400V, V_{GS}=0V$			25	$\mu A$
Gate-Source Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 20V$			$\pm 100$	nA
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	Reference to $25^\circ C, I_D=1.0mA$		0.78		$V/^\circ C$
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0		4.0	V
Static Drain-Source On Resistance (Note)	$R_{DS(ON)}$	$V_{GS}=10V, I_D=14A$			270	m $\Omega$
		$V_{GS}=10V, I_D=21A$			310	
<b>DYNAMIC PARAMETERS</b>						
Input Capacitance	$C_{ISS}$	$V_{DS}=25V, V_{GS}=0V, f=1.0MHz$		4300		pF
Output Capacitance	$C_{OSS}$			1000		
Reverse Transfer Capacitance	$C_{RSS}$			250		
<b>SWITCHING PARAMETERS</b>						
Total Gate Charge	$Q_G$	$V_{DS}=250V, V_{GS}=10V, I_D=21A$	84		190	nC
Gate Source Charge	$Q_{GS}$		12		27	
Gate Drain Charge	$Q_{GD}$		60		135	
Turn-ON Delay Time	$t_{D(ON)}$	$V_{DD}=250V, I_D=21A, R_G=2.35\Omega$			35	ns
Turn-ON Rise Time	$t_R$				120	
Turn-OFF Delay Time	$t_{D(OFF)}$				130	
Turn-OFF Fall-Time	$t_F$				98	
<b>SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS</b>						
Drain-Source Diode Forward Voltage	$V_{SD}$	$I_S=21A, V_{GS}=0V, T_J=25^\circ C$			1.8	V
Maximum Continuous Drain-Source Diode Forward Current	$I_S$				21	A
Maximum Pulsed Drain-Source Diode Forward Current	$I_{SM}$				84	
Reverse Recovery Time	$t_{RR}$	$I_F=21A, di/dt=100A/\mu s,$			580	ns
Reverse Recovery Charge	$Q_{RR}$	$T_J=25^\circ C, V_{DD}\leq 50V$ (Note)			8.1	$\mu C$

Note: Pulse Test: Pulse width  $\leq 300\mu s$ , Duty cycle  $\leq 2\%$



## ■ TYPICAL CHARACTERISTICS



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